

PROCESS AND APPARATUS FOR TREATING GAS CONTAINING  
FLUORINE-CONTAINING COMPOUNDS AND CO.

ABSTRACT OF THE DISCLOSURE

- The purpose of the present invention is to provide a
- 5 process and an apparatus for efficiently treating a gas containing fluorine-containing compounds and CO to be discharged, for example, from the step of dry cleaning the inner surfaces and the like of a semiconductor manufacturing apparatus or the step of etching various
- 10 types of formed films such as oxide films in the semiconductor industry. In order to accomplish the above-mentioned purpose, the gas treating process according to the present invention is a process for treating a gas containing fluorine-containing compounds and CO which
- 15 comprises contacting the above described gas with O<sub>2</sub> and H<sub>2</sub>O at a temperature of 850°C or higher to oxidize the CO to CO<sub>2</sub>; and then contacting the gas with γ-alumina at a temperature of 600 to 900°C to decompose the fluorine-containing compounds.